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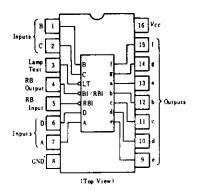
The HD74LS249 is 16-pin versions of the HD74LS49, respectively. Included in the HD74LS249 circuits is the full functional capability for lamp test and ripple blanking, which is not available in the HD74LS circuits. The HD74LS49 composes the and without tails and the HD74LS249 composes the and without tails. Composition of all other characters, including display patterns for BCD inputs above nine, is identical. The HD74LS249 features active-low outputs designed for driving indicators directly. All of the circuits have full ripple-blanking input/output controls and a lamp test input. Segment identification and resultant displays are shown below. Display patterns for BCD input counts above 9 are unique symbols to authenticate input conditions. This circuit incorporates automatic leading and/or trailing-edge zero-blanking control (RBI and RBO).

Lamp test (LT) of this type may be performed at any time when the BI/RBO node is at a high level. This type contains an overriding blanking input (BI) which can be used to control the lamp intensity be pulsing or to inhibit the outputs.

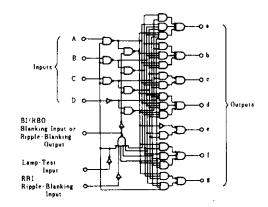
■ABSOLUTE MAXIMUM RATINGS

Item	Sym bol	Ratings	Unit
Supply voltage	Vcc	7.0	V
Input voltage	VIN	7.0	V
Output current (off-state)	I0(*ff)	1	m A
Operating temperature range	Tope	-20-+75	,C
Storage temperature range	Tris	-65~+150	°C

PIN ARRANGEMENT



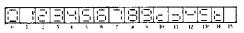
■BLOCK DIAGRAM



ERECOMMENDED OPERATING CONDITIONS

Item		Symbol	min	typ	max	Unit
Output voltage	a~g	Voн	-	-	5.5	v
	BI/RBO	Іон	-	_	- 50	μA
Output current	a~g	r	-	_	8	A
	BI/RBO	IO L		<u> </u>	3.2	mA





HD74LS249

IFUNCTION TABLE

Decimal or			Inp	uts			BI/RBO				Outputs				Note
Function	LT	RBI	D	С	В	A	DI/ KDU	а	Ъ	С	d	e	f	g	Note
0	Н	H	L	L	L	L	Н	H	Н	H	Н	H	H	L	T
1	H	×	L	L	L	Н	Н	L	Н	Н	L	L	L	L	j
2	H	×	L	L	Н	Ĺ	Н	Н	Н	L	Н	Н	L	Н	
3	H	×	L	L	Н	Н	H	Н	Н	H	H	L	L	Н	
4	Н	×	L	Н	L	L	Н	L	Н	H	Ĺ	L	H	Н	
5	H	×	L	H	L	Н	Н	H	L	H	Н	L	Ĥ	Н	
6	H	×	L	Н	Н	L	Н	Н	L	Н	H	Н	Н	Н	
7	Н	×	L	Н	H	Н	Н	H	Н	Н	L	L	L	L	,
8	Н	×	Н	L	L	L	Н	Н	Н	Н	H	H	H	Н] 1
9	Н	×	Н	L	L	Н	H	H	Н	H	H	L	Н	Н	
10	H	×	Н	L	Н	L	H	L	L	L	H	H	L	H	
11	H	×	Н	L	Н	Н	Н	L	L	Н	H	L	L	H	
12	H	×	Н	Н	L.	L	Н	L	H	L	L	L	H	H	
13	H	×	Н	Н	L	Н	Н	H	L	L	Н	L	H	Н	
14	H	×	H	H	Н	L	Н	L	L	L	H	Н	H	Н]
15	Н	×	Н	Н	Н	H	H	L	L	L	L _	L	L	L	
BI	×	×	×	×	×	×	L	L	L	L	L	L	L	L	2
RBI	Н	L	L	L	L	L	L	L	L	L	L	L	L	L	3
LT	L	×	×	×	×	×	Н	Н	Н	Н	Н	Н	Н	Н	4

H; high level, L; low level, X; irrelevant

Notes: 1. The blanking input (BI) must be open or held at a high logic level when output functions 0 through 15 are desired.

When a low logic level is applied directly to blanking input (BI), all segment outputs are low regardless of the level of any other input.

- When ripple-blanking input (RBI) and inputs A B, C, and D
 are at a low level with the lamp-test input high, all segment
 outputs go low and the ripple-blanking output (RBO) goes
 to a low level (response condition).
- When a blanking input/ripple blanking output (BI/RBO) is open or held high and a low is applied to the lamp-test input, all segment outputs are high.

ELECTRICAL CHARACTERISTICS ($Ta = -20 \sim +75^{\circ}$ C)

It	em	Symbol	Test Condition	s	min	typ*	max	Unit
Input voltage		VIH			2.0			V
		V11.					0.8	v
Output voltage	BI/RBO	Voн	$V_{CC} = 4.75 \text{V}, V_{IH} = 2 \text{V}, V_{IL} = 0.8 \text{V},$	<i>Ioн</i> = −50μ A	2.4	-	_	V
Output current	a~g	Іон	$V_{CC} = 4.75V$, $V_{IH} = 2V$, $V_{IL} = 0.8V$,	Von=5.5V	_		250	μА
Output voltage	D1 (DD)		1, 4 de 1, 1, 01, 1, 0 01, 1	IoL = 1.6mA	-		0.4	v
	BI/RBO	Vol	$V_{CC} = 4.75V, V_{IH} = 2V, V_{IL} = 0.8V$	IoL = 3.2mA	-	_	0.5	
	a~g		$V_{CC} = 4.75 \text{V}, V_{IH} = 2 \text{V}, V_{IL} = 0.8 \text{V}$	Io L = 4mA	_		0.4	
				IoL = 8mA	_	_	0.5	
	except BI/RBO	IIH	$V_{CC} = 5.25 \text{V}, V_I = 2.7 \text{V}$		_	20	μА	
	except BI/RBO				-		-0.4	
Input current	BI/RBO	ItL	$V_{CC} = 5.25 \text{V}, V_I = 0.4 \text{V}$			_	1.2	m A
	except BI/RBO	- Iı	$V_{CC} = 5.25 \text{V}, V_I = 7 \text{V}$		_	0.1	mA	
Short-circuit	BI/RBO	Ios	$V_{CC} = 5.25V$	-0.3		2	mΑ	
Supply current **		I cc	$V_{CC} = 5.25 \text{V}$		-	8	15	mΑ
Input clamp vol		VIK	$V_{CC} = 4.75 \text{V}, I_{IN} = -18 \text{mA}$	1	_	-	-1.5	V

^{*} V_{CC}=5V, Ta=25°C

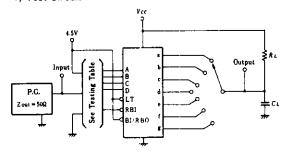
^{**} ICC is measured with all outputs open and all inputs at 4.5V.

ESWITCHING CHARACTERISTICS ($V_{CC} = 5V$, $T_a = 25^{\circ}C$)

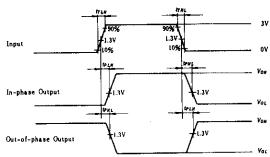
Item	Symbol	Input	Test Conditions	min	typ	max	Unit
	tрцн		C _L =15pF		-	100	
	t PHL	A	$R_L = 2k \Omega$	_	-	100	ns
Propagation delay time	IPLH .	DDI	C _L =15pF	_	_	100	ns
	tPHL	RBI	$R_L = 6 \text{k} \Omega$		_	100	

ETESTING METHOD

1) Test Circuit



Waveform



2) Testing Table

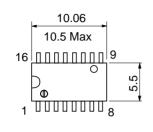
_			Outputs									
Item	RBI	D	С	В	Α	a	ь	С	d	e	f	g
	4.5V	GND	GND	GND	IN	OUT	-		OUT	OUT	OUT	
t PLH	4.5V	GND	GND	4.5V	IN	-	-	OUT	-	OUT	-	-
tPHL.	4.5V	GND	4.5V	4.5V	ΙN		OUT	_	OUT	OUT	OUT	OUT
	IN	GND	GND	GND	GND	OUT	оит	OUT	OUT	OUT	OUT	-

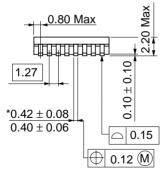
Notes) 1. Input pulse: $t_{TLH} \le 15$ ns, $t_{THL} \le 6$ ns, PRR = 1MHz, duty cycle=50%.

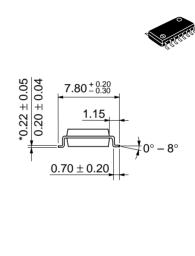
2. C_L includes probe and jig capacitance.

Unit: mm 19.20 20.00 Max 16 7.40 Max 6.30 1.3 1.11 Max 7.62 5.06 Max 2.54 Min 0.51 Min $0.25^{+0.13}_{-0.05}$ 0.48 ± 0.10 2.54 ± 0.25 $0^{\circ} - 15^{\circ}$ Hitachi Code DP-16 **JEDEC** Conforms EIAJ Conforms Weight (reference value) 1.07 g

Unit: mm







*Dimension including the plating thickness
Base material dimension

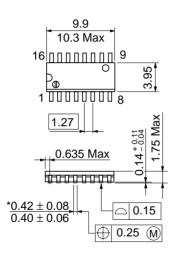
EIAJ Conforms
Weight (reference value) 0.24 g

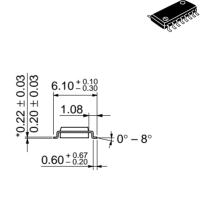
FP-16DA

Hitachi Code

JEDEC

Unit: mm





*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.15 g

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